Silicon NPN Power Transistors 2SC1295

DESCRIPTION

·With TO-3 package
·High voltage ,high speed

APPLICATIONS

·For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

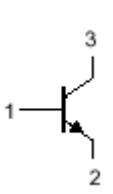

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	350	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2	A
P_T	Total power dissipation	T_C=25□	40	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0	350			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2 A;I_B=1A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=2 A;I_B=1A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1000V;I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V;I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1.5A ; V_{CE}=5V	3		13	

PACKAGE OUTLINE

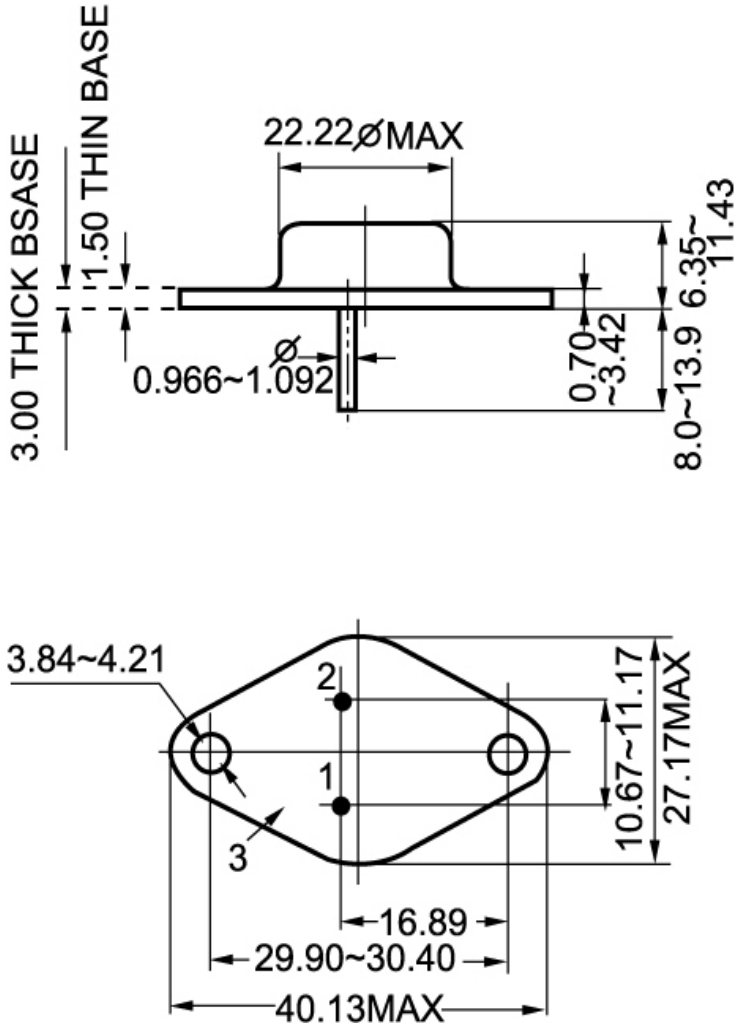

Fig.2 Outline dimensions